SEMIKRON

Absolute Maximum Ratings

Symbol	Conditions [1]	Values		Units
V_{CES}		1200		V
V_{CGR}	R_{GE} = 20 kΩ	1200		V
I_C	T_{case} = 25/80 °C	100 / 75		A
I_{CM}	T_{case} = 25/80 °C; t_p = 1 ms	200 / 150		A
V_{GES}		± 20		V
P_{tot}	per IGBT, T_{case} = 25 °C	625		W
T_j, (T_{stg})		– 40 . . .+150 (125)		°C
V_{isol}	AC, 1 min.	2 500 [7]		V
humidity	DIN 40 040	Class F		
climate	DIN IEC 68 T.1	55/150/56		
Inverse Diode			FWD [6]	
I_F= – I_C	T_{case} = 25/80 °C	95 / 65	130 / 90	A
I_{FM}= – I_{CM}	T_{case} = 25/80 °C; t_p = 1 ms	200 / 150	200 / 150	A
I_{FSM}	t_p = 10 ms; sin.; T_j = 150 °C	720	1100	A
I^2t	t_p = 10 ms; T_j = 150 °C	2600	6000	A^2s

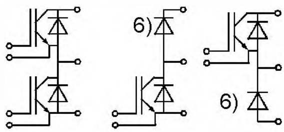
Characteristics

Symbol	Conditions [1]	min.	typ.	max.	Units
$V_{(BR)CES}$	V_{GE} = 0, I_C = 4 mA	≥ V_{CES}	–	–	V
$V_{GE(th)}$	V_{GE} = V_{CE}, I_C = 2 mA	4,5	5,5	6,5	V
I_{CES}	V_{GE} = 0 } T_j = 25 °C	–	0,1	1,5	mA
	V_{CE} = V_{CES} } T_j = 125 °C	–	6		mA
I_{GES}	V_{GE} = 20 V, V_{CE} = 0	–	–	300	nA
V_{CEsat}	I_C = 75 A } V_{GE} = 15 V;	–	2,5(3,1)	3(3,7)	V
V_{CEsat}	I_C = 100 A } T_j = 25 (125) °C	–	2,8(3,6)	–	V
g_{fs}	V_{CE} = 20 V, I_C = 75 A	31		–	S
C_{CHC}	per IGBT	–	–	350	pF
C_{ies}	V_{GE} = 0	–	5	6,6	nF
C_{oes}	V_{CE} = 25 V	–	720	900	pF
C_{res}	f = 1 MHz	–	380	500	pF
L_{CE}		–	–	30	nH
$t_{d(on)}$	V_{CC} = 600 V	–	30	60	ns
t_r	V_{GE} = +15 V, - 15 V [3]	–	70	140	ns
$t_{d(off)}$	I_C = 75 A, ind. load	–	450	600	ns
t_f	R_{Gon} = R_{Goff} = 15 Ω	–	70	90	ns
E_{on} [5]	T_j = 125 °C	–	10	–	mWs
E_{off} [5]		–	8	–	mWs
Inverse Diode [8]					
V_F = V_{EC}	I_F = 75 A } V_{GE} = 0 V;	–	2,0(1,8)	2,5	V
V_F = V_{EC}	I_F = 100 A } T_j = 25 (125) °C	–	2,25(2,05)	–	V
V_{TO}	T_j = 125 °C	–	–	1,2	V
r_T	T_j = 125 °C	–	12	15	mΩ
I_{RRM}	I_F = 75 A; T_j = 25 (125) °C [2]	–	27(40)	–	A
Q_{rr}	I_F = 75 A; T_j = 25 (125) °C [2]	–	3(10)	–	µC
FWD of types "GAL", "GAR" [8]					
V_F = V_{EC}	I_F = 75 A } V_{GE} = 0 V;	–	1,85(1,6)	2,2	V
V_F = V_{EC}	I_F = 100 A } T_j = 25 (125) °C	–	2,0(1,8)	–	V
V_{TO}	T_j = 125 °C	–	–	1,2	V
r_T	T_j = 125 °C	–	9	11	mΩ
I_{RRM}	I_F = 75 A; T_j = 25 (125) °C [2]	–	30(45)	–	A
Q_{rr}	I_F = 75 A; T_j = 25 (125) °C [2]	–	3,5(11)	–	µC
Thermal Characteristics					
R_{thjc}	per IGBT	–	–	0,2	°C/W
R_{thjc}	per diode / FWD "GAL; GAR"	–	–	0,50/0,36	°C/W
R_{thch}	per module	–	–	0,05	°C/W

SEMITRANS® M IGBT Modules

SKM 100 GB 123 D
SKM 100 GAL 123 D [6]
SKM 100 GAR 123 D [6]

SEMITRANS 2



GB GAL GAR

Features

- MOS input (voltage controlled)
- N channel, Homogeneous Si
- Low inductance case
- Very low tail current with low temperature dependence
- High short circuit capability, self limiting to 6 * I_{cnom}
- Latch-up free
- Fast & soft inverse CAL diodes[8]
- Isolated copper baseplate using DCB Direct Copper Bonding Technology
- Large clearance (10 mm) and creepage distances (20 mm).

Typical Applications: → B 6 - 45

- Switching (not for linear use)

1) T_{case} = 25 °C, unless otherwise specified

2) I_F = – I_C, V_R = 600 V, – di_F/dt = 800 A/µs, V_{GE} = 0 V

3) Use V_{GEoff} = -5 ... -15 V

5) See fig. 2 + 3; R_{Goff} = 15 Ω

6) The free-wheeling diodes of the GAL and GAR types have the data of the inverse diodes of SKM 150 GB 123 D

7) V_{isol} = 4000 V_{rms} on request

8) CAL = Controlled Axial Lifetime Technology.

Cases and mech. data → **B6 - 46**

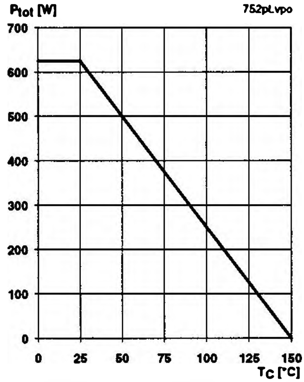
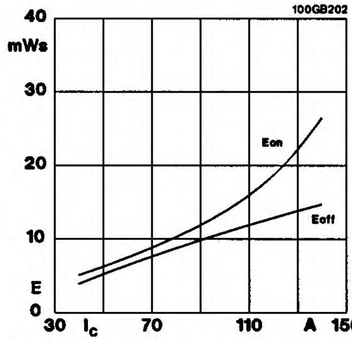
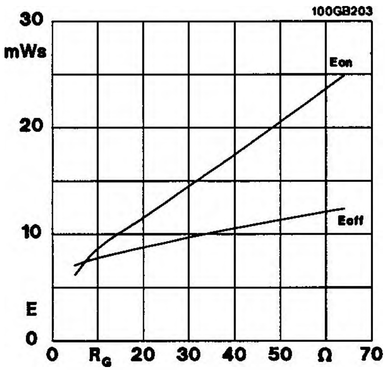


Fig. 1 Rated power dissipation $P_{tot} = f(T_C)$



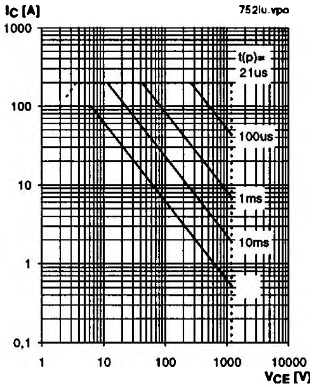
$T_j = 125$ °C
$V_{CE} = 600$ V
$V_{GE} = \pm 15$ V
$R_G = 15\ \Omega$

Fig. 2 Turn-on /-off energy = f (I_C)



$T_j = 125$ °C
$V_{CE} = 600$ V
$V_{GE} = \pm 15$ V
$I_C = 75$ A

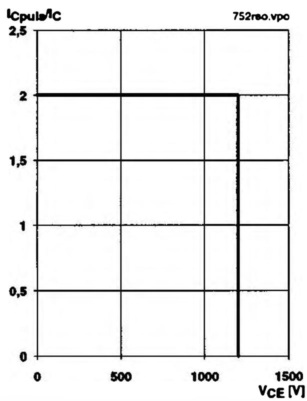
Fig. 3 Turn-on /-off energy = f (R_G)



1 pulse
$T_C = 25$ °C
$T_j \leq 150$ °C

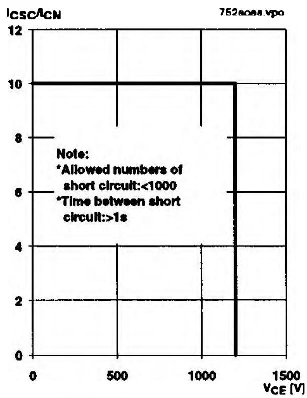
Not for linear use

Fig. 4 Maximum safe operating area (SOA) $I_C = f(V_{CE})$



$T_j \leq 150$ °C
$V_{GE} = 15$ V
$R_{g(off)} = 15\ \Omega$
$I_C = 75$ A

Fig. 5 Turn-off safe operating area (RBSOA)



$T_j \leq 150$ °C
$V_{GE} = \pm 15$ V
$t_{sc} \leq 10$ µs
$L < 25$ nH
$I_{CN} = 75$ A

Fig. 6 Safe operating area at short circuit $I_C = f(V_{CE})$

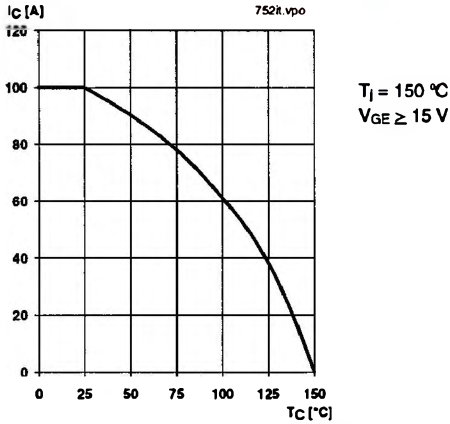


Fig. 8 Rated current vs. temperature $I_C = f(T_C)$

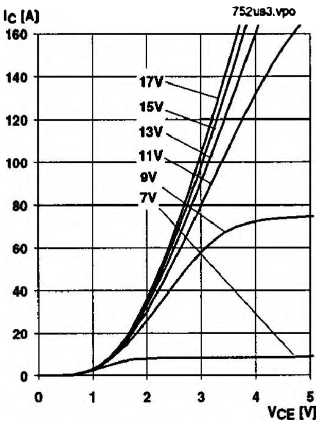


Fig. 9 Typ. output characteristic, t_p = 80 µs; 25 °C

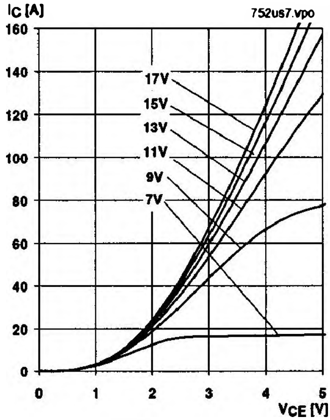


Fig. 10 Typ. output characteristic, t_p = 80 µs; 125 °C

$P_{cond(t)} = V_{CEsat(t)} \cdot I_{C(t)}$

$V_{CEsat(t)} = V_{CE(TO)(Tj)} + r_{CE(Tj)} \cdot I_{C(t)}$

$V_{CE(TO)(Tj)} \leq 1{,}5 + 0{,}002\ (T_j - 25)$ [V]

$r_{CE(Tj)} = 0{,}013 + 0{,}00006\ (T_j - 25)$ [Ω]

valid for $V_{GE} = +\,15^{+2}_{-1}$ [V]; $I_C > 0{,}3\ I_{Cnom}$

Fig. 11 Typ. saturation characteristic (IGBT)
Calculation elements and equations

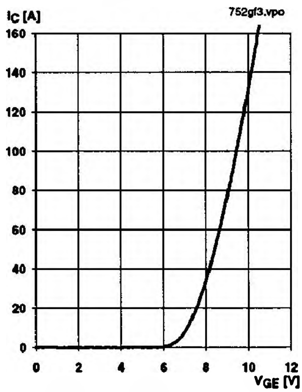
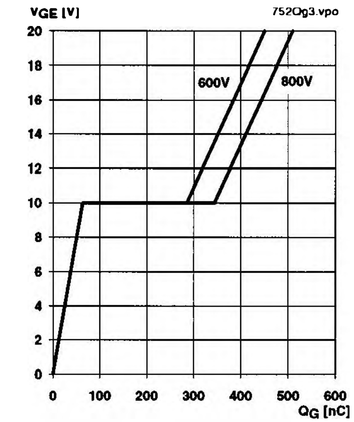
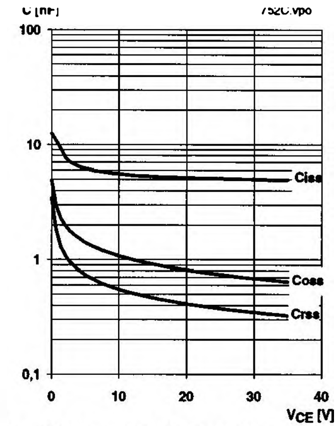


Fig. 12 Typ. transfer characteristic, t_p = 80 µs; V_{CE} = 20 V



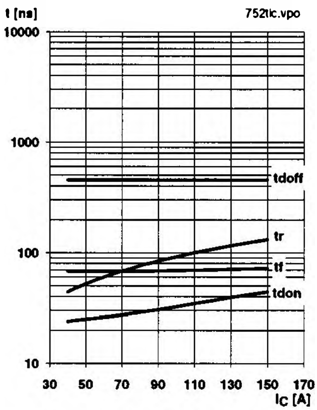
I_{Cpuls} = 75 A

Fig. 13 Typ. gate charge characteristic



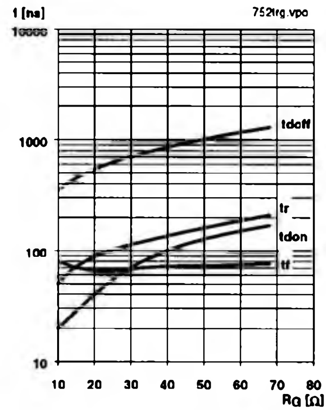
V_{GE} = 0 V
f = 1 MHZ

Fig. 14 Typ. capacitances vs.V_{CE}



T_j = 125 °C
V_{CE} = 600 V
V_{GE} = ± 15 V
R_{gon} = 15 Ω
R_{goff} = 15 Ω
induct. load

Fig. 15 Typ. switching times vs. I_C



T_j = 125 °C
V_{CE} = 600 V
V_{GE} = ± 15 V
I_C = 75 A
induct. load

Fig. 16 Typ. switching times vs. gate resistor R_G

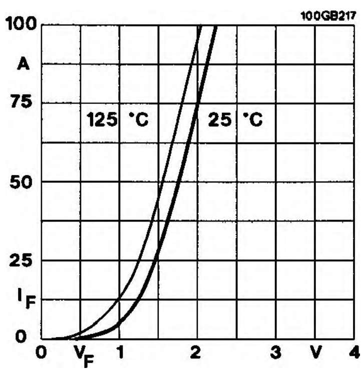


Fig. 17 Typ. CAL diode forward characteristic

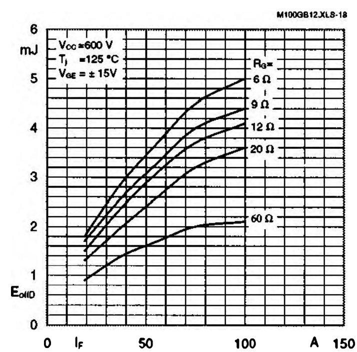


Fig. 18 Diode turn-off energy dissipation per pulse

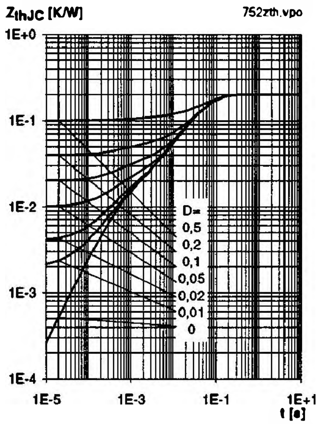


Fig. 19 Transient thermal impedance of IGBT $Z_{thJC} = f(t_p)$; $D = t_p / t_c = t_p \cdot f$

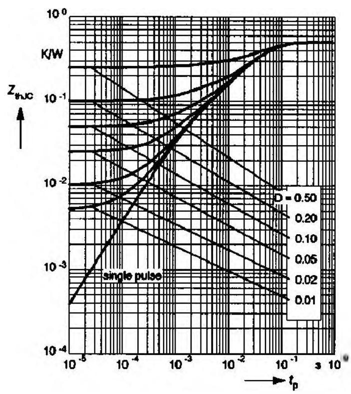


Fig. 20 Transient thermal impedance of inverse CAL diodes $Z_{thJC} = f(t_p)$; $D = t_p / t_c = t_p \cdot f$

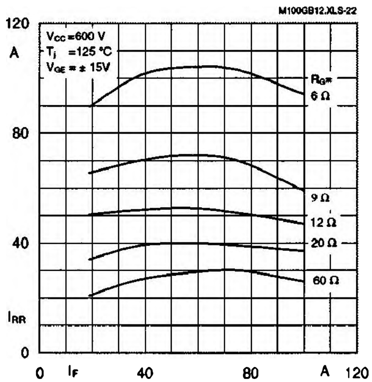


Fig. 22 Typ. CAL diode peak reverse recovery current $I_{RR} = f(I_F; R_G)$

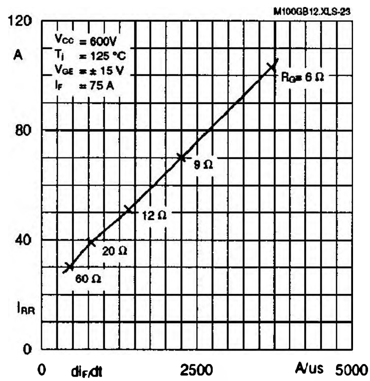


Fig. 23 Typ. CAL diode peak reverse recovery current $I_{RR} = f(di_F/dt)$

Typical Applications include

Switched mode power supplies

DC servo and robot drives

Inverters

DC choppers (versions GAR; GAL)

AC motor speed control

Inductive heating

UPS Uninterruptable power supplies

General power switching applications

Electronic (also portable) welders

Pulse frequencies also above 15 kHz

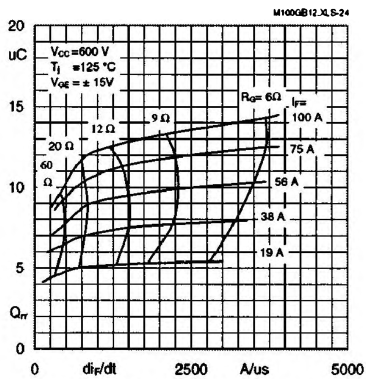
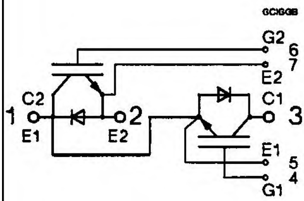
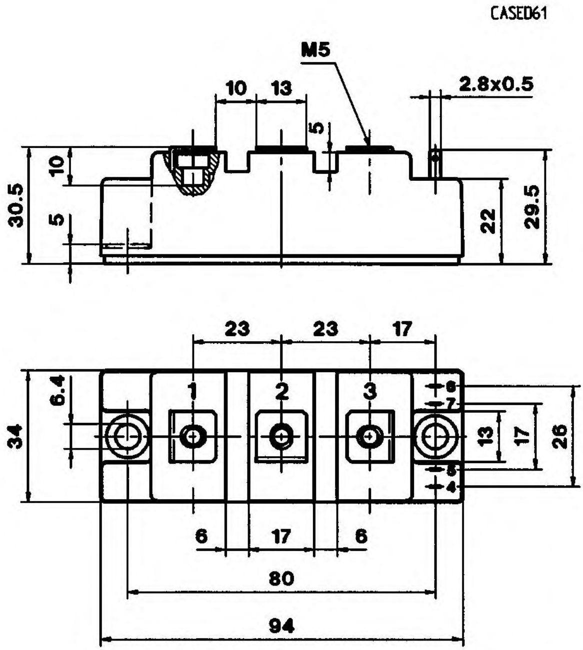


Fig. 24 Typ. CAL diode recovered charge $Q_{rr} = f(di/dt)$

SEMITRANS 2
Case D 61
UL Recognized
File no. E 63 532

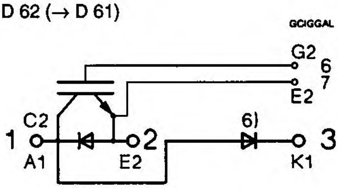
SKM 100 GB 123 D
SKM 100 GB 173 D



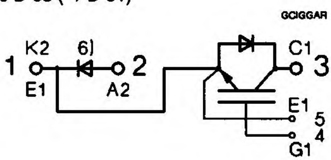


Dimensions in mm

SKM 100 GAL 123 D
Case D 62 (→ D 61)



SKM 100 GAR 123 D
Case D 63 (→ D 61)



Case outline and circuit diagrams

Mechanical Data						
Symbol	**Conditions**		**Values min.**	**typ.**	**max.**	**Units**
M_1	to heatsink, SI Units	(M6)	3	–	5	Nm
	to heatsink, US Units		27	–	44	lb.in.
M_2	for terminals, SI Units	(M5)	2,5	–	5	Nm
	for terminals US Units		22	–	44	lb.in.
a			–	–	5x9,81	m/s^2
w			–	–	250	g

6) Freewheeling diode → page B 6 - 41, remark 6.

This is an electrostatic discharge sensitive device (ESDS). Please observe the international standard IEC 747-1, Chapter IX.

Eight devices are supplied in one SEMIBOX A without mounting hardware, which can be ordered separately under Ident No. 33321100 (for 10 SEMITRANS 2). Larger packing units of 20 and 42 pieces are used if suitable

Accessories → page B 6 - 4.
SEMIBOX → page C - 1.

